

U.S. Department of Commerce, Patent and Trademark Office		Atty Docket No.	Serial No.
		NS-4971 US	09/903,059
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Applicant	
(Use several sheets if necessary)		Bulucea, Constantin	
		Filing Date	Group
		July 10, 2001	2814
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)			
DF	AA	Andreani, et al., "A 1.8-GHZ CMOS VCO Tuned by an Accumulation-Mode MOS Varactor," IEEE Intl. Symposium on Circuits and Systems, 28 - 31 May 2000, pp. 1-315 - 1 - 318.	
DF	AB	Grove, <u>Physics and Technology of Semiconductor Devices</u> (John Wiley & Sons), 1967, pp. 263 - 305.	
DF	AC	Grove, et al., "Effect of Surface Fields on the Breakdown Voltage of Planar Silicon <i>p-n</i> Junction," <u>IEEE Trans. Electron Devices</u> , Vol. ED-14, 1967, pp. 157 - 162.	
DF	AD	Grove, et al., "Surface Effects on <i>p-n</i> Junctions: Characteristics of Surface Space-Charge Regions Under Non-Equilibrium Conditions," <u>Solid-State Electronics</u> , Vol. 9, 1966, pp. 783 - 806.	
DF	AE	Kral, et al., "RF-CMOS Oscillators with Switched Tuning," <u>Procs. IEEE Custom Integrated Circuits Conference</u> , 1998, pp. 555 - 558.	
DF	AF	Lee, <u>The Design of CMOS Radio-Frequency Integrated Circuits</u> (Cambridge Univ. Press), 1998, pp. 37 - 41 and 504 - 514.	
DF	AG	McMahon, et al., "Voltage-Sensitive Semiconductor Capacitors," <u>1958 IRE Wescon Conf. Rec.</u> , Part 3, 19 - 22 August 1958, pp. 72 - 82.	
DF	AH	Moll, "Variable Capacitance With Large Capacity Change", <u>IRE Wescon Conf. Rec.</u> , Vol. 3, 1959, pp. 32 - 36.	
DF	AI	Ng, <u>Complete Guide to Semiconductor Devices</u> (McGraw Hill), 1995, pp. 11 - 22.	
DF	AJ	Razavi, <u>Design of Analog CMOS Integrated Circuits</u> (McGraw Hill), 2001, pp. 495 - 525.	
DF	AK	Rusu et al., "Deep-Depletion Breakdown Voltage of Silicon-Dioxide/Silicon MOS Capacitors", <u>IEEE Trans. Elec. Devs.</u> , March 1979, pp. 201 - 205.	
DF	AL	Rusu et al., "Reversible Breakdown Voltage Collapse in Silicon Gate-Controlled Diodes" <u>Solid-State Electronics</u> , Vol. 23, 1980, pp. 473 - 480.	
DF	AM	Svelto, et al., "A Three Terminal Varactor for RF IC's in Standard CMOS Technology," <u>IEEE Transactions on Electron Devices</u> , Vol. 47, 2000, pp. 893 - 895.	
Examiner <i>[Signature]</i>		Date Considered 8/23/02	
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.			

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DF	AN	Warner, Jr., et al., <u>Transistors – Fundamentals for the Integrated-Circuit Engineer</u> (John Wiley & Sons), 1983, pp. 320 – 321.	
DF	AO	Wong et al., "A Wide Tuning Range Gated Varactor", <u>IEEE J. Solid State Circs.</u> , May, 2000, pp. 773 – 779.	
Examiner <i>Da Shin</i>		Date Considered <i>8/23/02</i>	
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